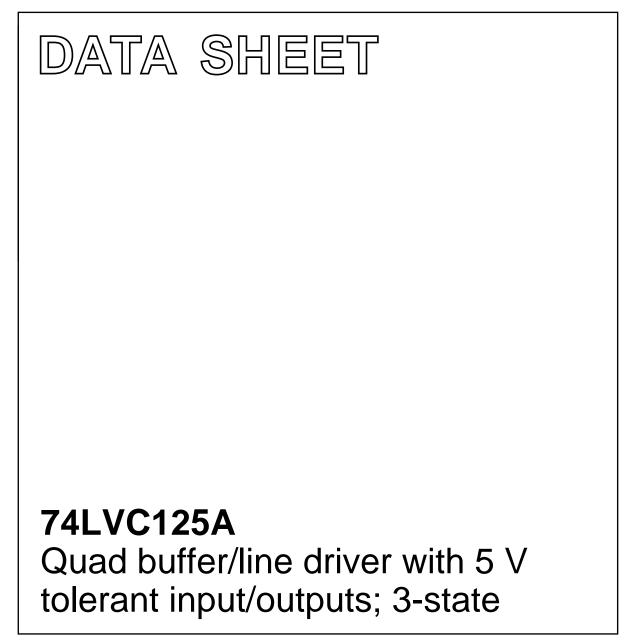
INTEGRATED CIRCUITS



Product specification Supersedes data of 2002 Mar 08 2003 May 07

Philips Semiconductors





74LVC125A

FEATURES

- 5 V tolerant inputs/outputs for interfacing with 5 V logic
- Wide supply voltage range from 1.2 to 3.6 V
- CMOS low power consumption
- Direct interface with TTL levels
- Inputs accept voltages up to 5.5 V
- Complies with JEDEC standard no. 8-1A
- ESD protection: HBM EIA/JESD22-A114-A exceeds 2000 V MM EIA/JESD22-A115-A exceeds 200 V
- Specified from -40 to +85 °C and -40 to +125 °C.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25 \text{ °C}$; $t_r = t_f \le 2.5 \text{ ns.}$

DESCRIPTION

The 74LVC125A is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. In 3-state operation, outputs can handle 5 V.

The 74LVC125A consists of four non-inverting buffers/line drivers with 3-state outputs (nY) which are controlled by the output enable input ($n\overline{OE}$). A HIGH at $n\overline{OE}$ causes the outputs to assume a high-impedance OFF-state.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	propagation delay nA to nY	$C_L = 50 \text{ pF}; V_{CC} = 3.3 \text{ V}$	2.4	ns
CI	input capacitance		4.0	pF
C _{PD}	power dissipation capacitance per gate	$V_{CC} = 3.3 V;$ notes 1 and 2	12	pF

Notes

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

f_i = input frequency in MHz;

fo = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

N = total load switching outputs;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

2. The condition is $V_I = GND$ to V_{CC} .

ORDERING INFORMATION

	PACKAGES							
I TPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE			
74LVC125AD	–40 to +125 °C	14	SO14	plastic	SOT108-1			
74LVC125ADB	−40 to +125 °C	14	SSOP14	plastic	SOT337-1			
74LVC125APW	–40 to +125 °C	14	TSSOP14	plastic	SOT402-1			
74LVC125ABQ	−40 to +125 °C	14	DHVQFN14	plastic	SOT762-1			

74LVC125A

FUNCTION TABLE

See note 1.

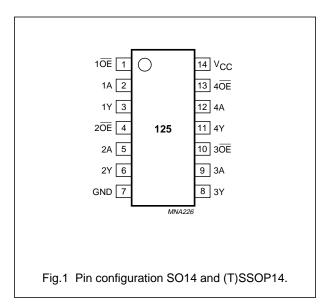
INF	OUTPUT	
nŌE	nA	nY
L	L	L
L	Н	Н
Н	Х	Z

Note

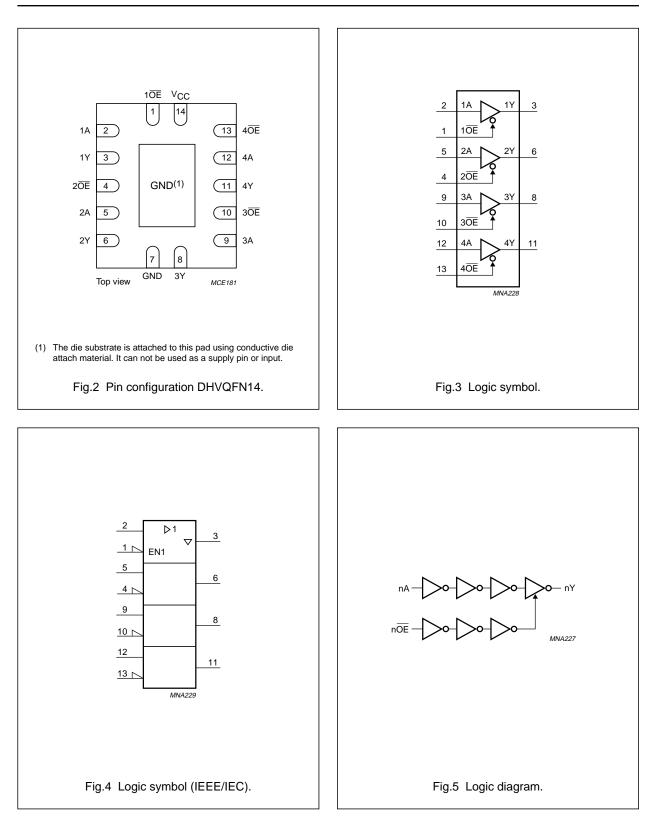
- 1. H = HIGH voltage level;
 - L = LOW voltage level;
 - X = don't care;
 - Z = high-impedance OFF-state.

PINNING

PIN	SYMBOL	DESCRIPTION
1	1 0E	data enable input (active LOW)
2	1A	data input
3	1Y	data output
4	2 <mark>0E</mark>	data enable input (active LOW)
5	2A	data input
6	2Y	data output
7	GND	ground (0 V)
8	3Y	data output
9	3A	data input
10	3 <mark>OE</mark>	data enable input (active LOW)
11	4Y	data output
12	4A	data input
13	4 0E	data enable input (active LOW)
14	V _{CC}	supply voltage



74LVC125A



74LVC125A

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage	for maximum speed performance	2.7	3.6	V
		for low voltage applications	1.2	3.6	V
VI	input voltage		0	5.5	V
Vo	output voltage	output HIGH or LOW state	0	V _{CC}	V
		output 3-state	0	5.5	V
T _{amb}	operating ambient temperature		-40	+125	°C
t _r , t _f	input rise and fall times	$V_{CC} = 1.2 \text{ to } 2.7 \text{ V}$	0	20	ns/V
		V _{CC} = 2.7 to 3.6 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input diode current	V ₁ < 0	-	-50	mA
VI	input voltage	note 1	-0.5	+6.5	V
I _{ОК}	output diode current	$V_{\rm O} > V_{\rm CC}$ or $V_{\rm O} < 0$	-	±50	mA
Vo	output voltage	output HIGH or LOW state; note 1	-0.5	V _{CC} + 0.5	V
		output 3-state; note 1	-0.5	+6.5	V
I _O	output source or sink current	$V_{O} = 0$ to V_{CC}	-	±50	mA
I _{CC} , I _{GND}	V _{CC} or GND current		-	±100	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	power dissipation	$T_{amb} = -40$ to +125 °C; note 2	-	500	mW

Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. For SO14 packages: above 70 °C derate linearly with 8 mW/K.

For SSOP14 and TSSOP14 packages: above 60 °C derate linearly with 5.5 mW/K.

For DHVQFN14 packages: above 60 °C derate linearly with 4.5 mW/K.

74LVC125A

DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDITI	ONS		TYP. ⁽¹⁾	MAX.	UNIT
SYMBOL	PARAMETER	OTHER	V _{CC} (V)	- MIN.			
T _{amb} = -40	0 to +85 °C			•	1		•
VIH	HIGH-level input voltage		1.2	V _{CC}	-	-	V
			2.7 to 3.6	2.0	-	-	V
V _{IL}	LOW-level input voltage		1.2	-	-	GND	V
			2.7 to 3.6	-	-	0.8	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		I _O = −100 μA	2.7 to 3.6	V _{CC} - 0.2	V _{CC}	-	V
		I _O = -12 mA	2.7	V _{CC} - 0.5	-	-	V
		I _O = -18 mA	3.0	V _{CC} – 0.6	-	-	V
		I _O = -24 mA	3.0	V _{CC} - 0.8	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		I _O = 100 μA	2.7 to 3.6	-	GND	0.2	V
		I _O = 12 mA	2.7	-	-	0.4	V
		I _O = 24 mA	3.0	-	-	0.55	V
I _{LI}	input leakage current	$V_{I} = 5.5 V \text{ or GND}$	3.6	-	±0.1	±5	μA
I _{OZ}	3-state output OFF-state current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = 5.5 \text{ V or GND};$ note 2	3.6	-	±0.1	±5	μA
I _{off}	power off leakage supply	$V_{\rm I}$ or $V_{\rm O}$ = 5.5 V	0.0	-	±0.1	±10	μA
I _{CC}	quiescent supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$	3.6	-	0.1	10	μA
ΔI_{CC}	additional quiescent supply current per input pin	$V_{I} = V_{CC} - 0.6 V; I_{O} = 0$	2.7 to 3.6	-	5	500	μΑ

74LVC125A

0)/// 0		TEST CONDITIONS			TYP. ⁽¹⁾	MAX.	
SYMBOL	PARAMETER	OTHER V _{CC} (V)		– MIN.			
T _{amb} = -4	0 to +125 °C						•
V _{IH}	HIGH-level input voltage		1.2	V _{CC}	-	-	V
			2.7 to 3.6	2.0	-	-	V
V _{IL}	LOW-level input voltage		1.2	-	-	GND	V
			2.7 to 3.6	-	-	0.8	V
V _{OH}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		I _O = −100 μA	2.7 to 3.6	V _{CC} – 0.3	-	-	V
		I _O = -12 mA	2.7	V _{CC} - 0.65	-	-	V
		I _O = -18 mA	3.0	V _{CC} - 0.75	-	-	V
		I _O = -24 mA	3.0	V _{CC} – 1	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$					
		I _O = 100 μA	2.7 to 3.6	-	-	0.3	V
		I _O = 12 mA	2.7	-	-	0.6	V
		I _O = 24 mA	3.0	-	-	0.8	V
ILI	input leakage current	$V_{I} = 5.5 V \text{ or GND}$	3.6	-	-	±20	μA
I _{OZ}	3-state output OFF-state current	$V_I = V_{IH} \text{ or } V_{IL};$ $V_O = 5.5 \text{ V or GND};$ note 2	3.6	-	-	±20	μA
I _{off}	power off leakage supply	$V_{\rm I}$ or $V_{\rm O}$ = 5.5 V	0.0	-	-	±20	μA
I _{CC}	quiescent supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$	3.6	-	-	40	μA
Δl _{CC}	additional quiescent supply current per input pin	$V_{I} = V_{CC} - 0.6 V; I_{O} = 0$	2.7 to 3.6	-	-	5000	μA

Notes

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

2. For I/O ports the parameter I_{OZ} includes the input leakage current.

74LVC125A

AC CHARACTERISTICS

 $GND = 0 \text{ V}; t_r = t_f \leq 2.5 \text{ ns.}$

	DADAMETED	TEST CONDITIONS		MIN	TVD			
SYMBOL	PARAMETER	WAVEFORMS	V _{cc} (V)	MIN.	TYP.	MAX.	UNIT	
T _{amb} = -40) to +85 °C					1		
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 6 and 8	1.2	-	12	-	ns	
			2.7	1.5	2.7	5.5	ns	
			3.0 to 3.6	1.0	2.4 ⁽¹⁾	4.8	ns	
t _{PZH} /t _{PZL}	3-state output enable time $n\overline{OE}$ to nY	see Figs 7 and 8	1.2	_	16	-	ns	
			2.7	1.5	3.5	6.6	ns	
			3.0 to 3.6	1.0	2.8 ⁽¹⁾	5.4	ns	
t _{PHZ} /t _{PLZ}	3-state output disable time $n\overline{OE}$ to nY	see Figs 7 and 8	1.2	_	7.0	-	ns	
			2.7	1.5	3.0	5.0	ns	
			3.0 to 3.6	1.0	2.7 ⁽¹⁾	4.6	ns	
t _{sk(0)}	skew	note 2		-	-	1.0	ns	
$T_{amb} = -40$) to +125 °C							
t _{PHL} /t _{PLH}	propagation delay nA to nY	see Figs 6 and 8	1.2	-	-	-	ns	
			2.7	1.5	-	7.0	ns	
			3.0 to 3.6	1.0	_	6.0	ns	
t _{PZH} /t _{PZL}	3-state output enable time $n\overline{OE}$ to nY	see Figs 7 and 8	1.2	-	_	-	ns	
			2.7	1.5	_	8.5	ns	
			3.0 to 3.6	1.0	-	7.0	ns	
t _{PHZ} /t _{PLZ}	3-state output disable time $n\overline{OE}$ to nY	see Figs 7 and 8	1.2	-	-	-	ns	
			2.7	1.5	-	6.5	ns	
			3.0 to 3.6	1.0	-	6.0	ns	
t _{sk(0)}	skew	note 2		-	_	1.5	ns	

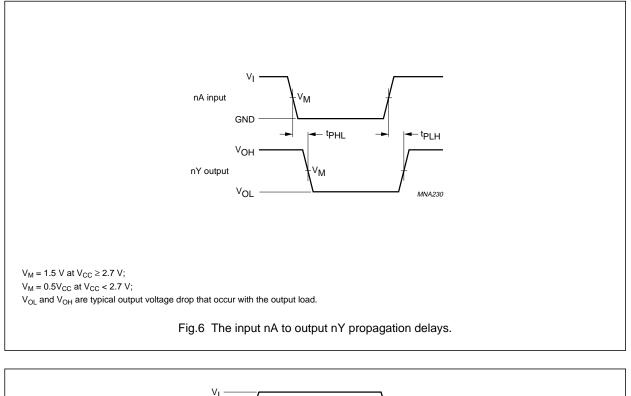
Notes

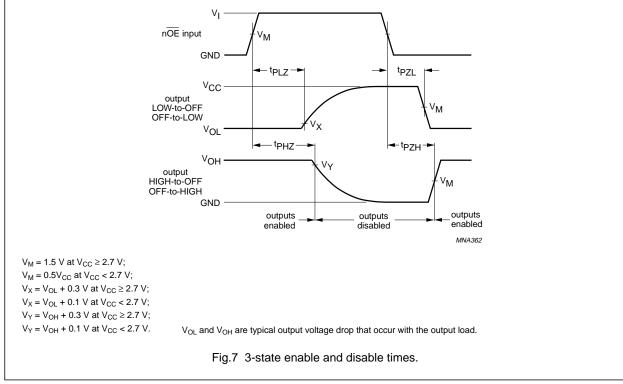
1. All typical values are measured at V_{CC} = 3.3 V.

2. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

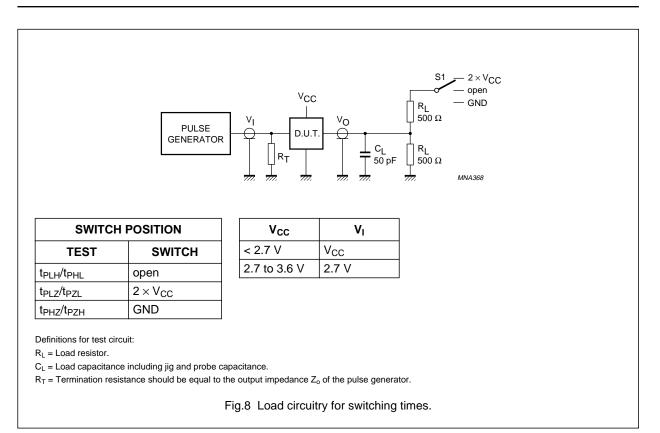
74LVC125A

AC WAVEFORMS





74LVC125A

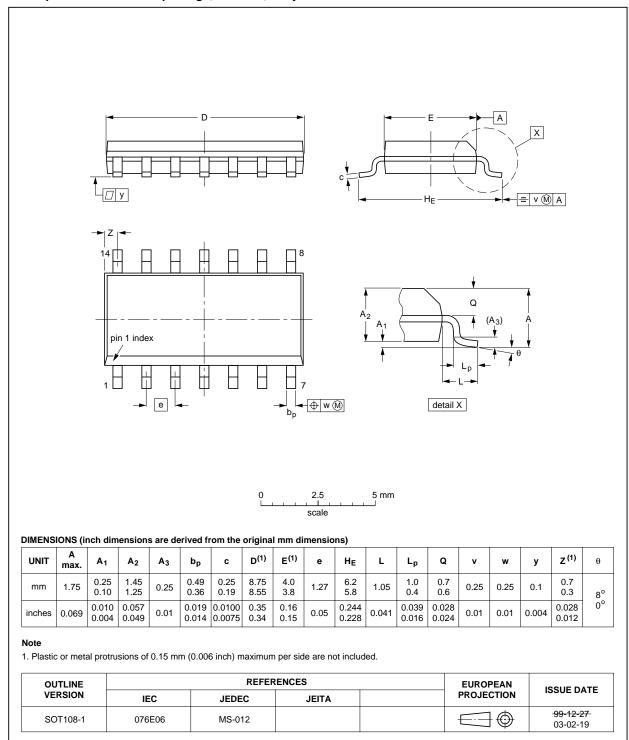


74LVC125A

Quad buffer/line driver with 5 V tolerant input/outputs; 3-state

PACKAGE OUTLINES

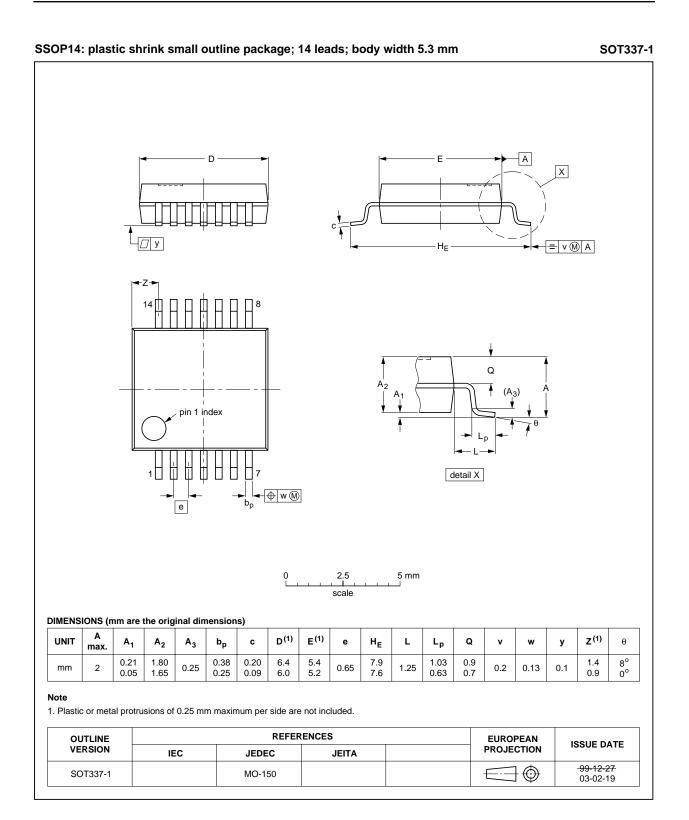
SO14: plastic small outline package; 14 leads; body width 3.9 mm



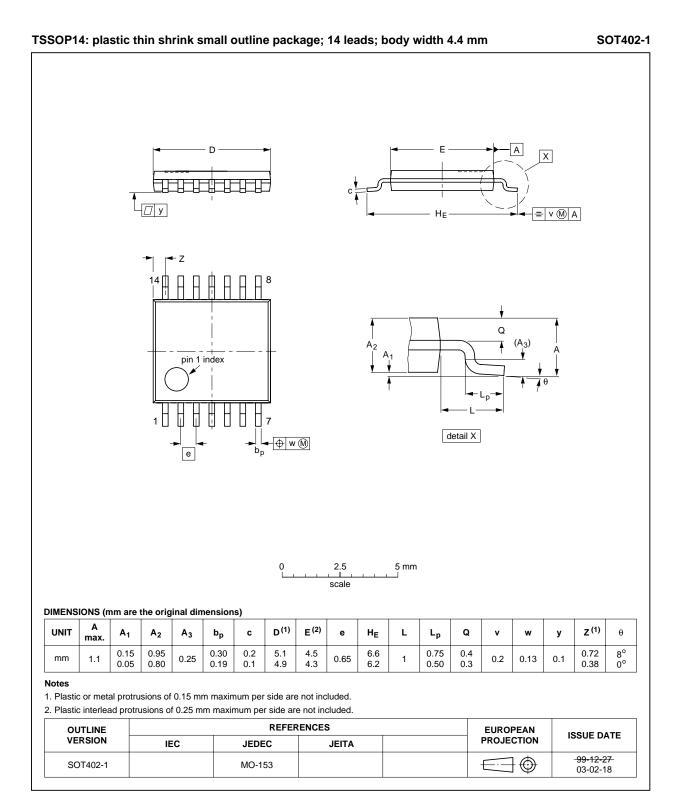
SOT108-1

74LVC125A

Quad buffer/line driver with 5 V tolerant input/outputs; 3-state



74LVC125A



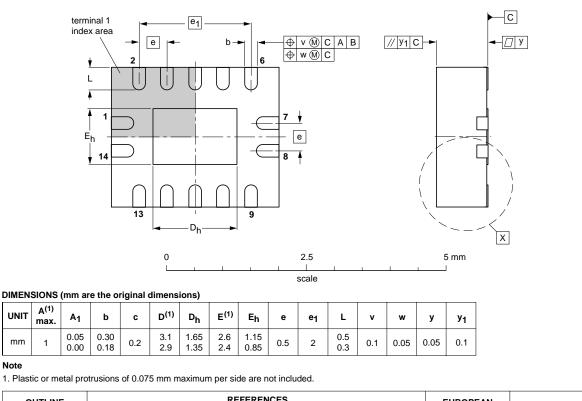
terminal 1 index area

Quad buffer/line driver with 5 V tolerant input/outputs; 3-state

74LVC125A

detail X

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1



OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	IEC JEDEC JEITA			PROJECTION	1330E DATE
SOT762-1		MO-241				-02-10-17- 03-01-27
	1		1			

74LVC125A

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferably be kept:

- below 220 °C for all the BGA packages and packages with a thickness ≥ 2.5mm and packages with a thickness <2.5 mm and a volume ≥350 mm³ so called thick/large packages
- below 235 °C for packages with a thickness <2.5 mm and a volume <350 mm³ so called small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^{\circ}$ C.

Suitability of surface mount IC packages for wave and reflow soldering methods

	SOLDERING METHOD		
FACTAGE	WAVE	REFLOW ⁽²⁾	
BGA, LBGA, LFBGA, SQFP, TFBGA, VFBGA	not suitable	suitable	
DHVQFN, HBCC, HBGA, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, HVQFN, HVSON, SMS	not suitable ⁽³⁾	suitable	
PLCC ⁽⁴⁾ , SO, SOJ	suitable	suitable	
LQFP, QFP, TQFP	not recommended ⁽⁴⁾⁽⁵⁾	suitable	
SSOP, TSSOP, VSO, VSSOP	not recommended ⁽⁶⁾	suitable	

Notes

- 1. For more detailed information on the BGA packages refer to the "(*LF*)BGA Application Note" (AN01026); order a copy from your Philips Semiconductors sales office.
- 2. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 3. These packages are not suitable for wave soldering. On versions with the heatsink on the bottom side, the solder cannot penetrate between the printed-circuit board and the heatsink. On versions with the heatsink on the top side, the solder might be deposited on the heatsink surface.
- 4. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 5. Wave soldering is suitable for LQFP, TQFP and QFP packages with a pitch (e) larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 6. Wave soldering is suitable for SSOP, TSSOP, VSO and VSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

74LVC125A

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products including circuits, standard cells, and/or software described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

NOTES

NOTES

Philips Semiconductors – a worldwide company

Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

© Koninklijke Philips Electronics N.V. 2003

SCA75

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

613508/04/pp20

Date of release: 2003 May 07

Document order number: 9397 750 10532

Let's make things better.





Semiconductors

Philips